

NTE2430
Silicon NPN Transistor
High Voltage Amp/Switch
(Compl to NTE2431)

Description:

The NTE2430 is a silicon NPN transistor in a SOT-89 type surface mount package designed for use in amplifier and switching applications.

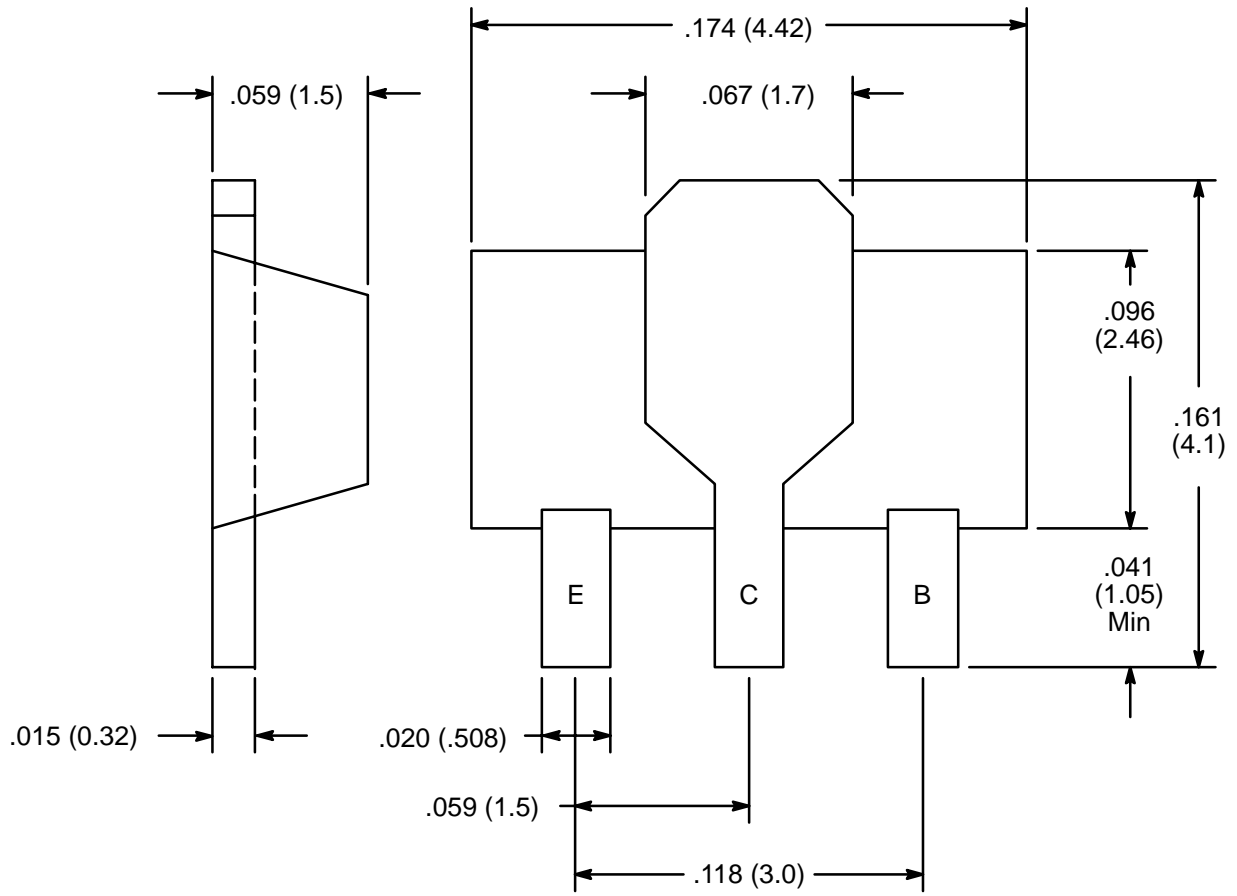
Absolute Maximum Ratings:

Collector-Base Voltage (Open Emitter), V_{CBO}	400V
Collector-Emitter Voltage (Open Base), V_{CEO}	350V
Emitter-Base Voltage (Open Collector), V_{EBO}	5V
DC Collector Current, I_C	1A
Base Current, I_B	500mA
Total Power Dissipation ($T_A \leq +25^\circ\text{C}$, Note 1), P_{tot}	1W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Thermal Resistance, Junction-to-Ambient (Note 1), R_{thJA}	125K/W

Note 1. Device mounted on a ceramic substrate; area = 2.5cm², thickness = 0.7mm.

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 300\text{V}, I_B = 0$	-	-	20	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	-	-	10	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 4\text{mA}$	-	-	500	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}, I_B = 4\text{mA}$	-	-	1.3	V
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$	40	-	-	
Collector Capacitance	C_c	$I_E = I_e = 0, V_{CB} = 10, f = 1\text{MHz}$	-	-	2	pF
Transitional Frequency	f_T	$V_{CE} = 10\text{V}, I_C = 10\text{mA}, f = 5\text{MHz}$	70	-	-	MHz



Bottom View